

Supporting Information

An experimental and theoretical study on the electronic and structural properties of CdSe@TiO₂ nanotubes arrays

R. G. Freitas^{a,b}, F. W. S. Lucas^b, M. A. Santanna^b, R. A. Mendes^a, A. J. Terezo^a, G. L.
C. de Souza^{a,c}, L. H. Mascaro^b, E. C. Pereira^{b*}

^aDepartment of Chemistry, Federal University of Mato Grosso, Laboratório Computacional de Materiais, 78060-900, Cuiaba, MT, Brazil

^bDepartment of Chemistry, Federal University of São Carlos, Laboratório Interdisciplinar de Eletroquímica e Cerâmica, P. O. Box 676, 13560-970 São Carlos, SP, Brazil

^cInstitute of Exact Sciences and Technology, Federal University of Amazonas, CEP 69100-000, Itacoatiara, AM, Brazil

* Corresponding author: Tel.: +55 16 3351 9309

E-mail address: ernesto@ufscar.br

Electrodeposition of CdSe into TiO₂NT

All chemicals used were of analytical grade and underwent no further purification: selenium oxide (SeO₂, Sigma-Aldrich 99.9%), cadmium sulphate (CdSO₄, Sigma-Aldrich 99.9%) and sulphuric acid (H₂SO₄, Alfa-Aesar 98%). Electrochemical experiments were carried out in a potentiostat/galvanostat (Autolab PGSTAT 302N, Metrohm-Eco Chemie) controlled by GPES[®] and FRA[®] software.

Firstly, the electrodeposition processes of the CdSe were evaluated by cyclic voltammetry on TiO₂NT. At a concentration of 1 mmol L⁻¹, the elements were analysed separately and, after that, the Cd²⁺ ions were studied in the presence of Se. After studies of the electrochemical deposition potential, the electrodeposition of all films was performed in a stationary bath at 25 °C using the pulsed deposition method and an electrolytic bath containing 5 mmol L⁻¹ Cd²⁺, 1 mmol L⁻¹ SeO₂, and 0.5 mol L⁻¹ H₂SO₄ (as supporting electrolyte). The ratio Cd/Se of 5/1 was selected in order to favour a stoichiometric obtaining of CdSe by an excess of Cd²⁺ ions [1]. Prior to deposition, the TiO₂NT working electrode was immersed in the electrolytic bath and ultrasonicated during 5 min for diffusing of the solution into the nanotubes.

The electrochemical behaviour of the individual Cd²⁺ and H₂SeO₃ species, as well as, of the binary system on the TiO₂NT surface were analysed, the cyclic voltammograms (CV) can be seen in Figure 1. The CV curves were recorded at 50 mV s⁻¹ from 0 V to 0.9 V vs. Ag/AgCl/Cl⁻_(sat. KCl) and the electrochemical profile of the working electrode was taken in SE at the same condition.

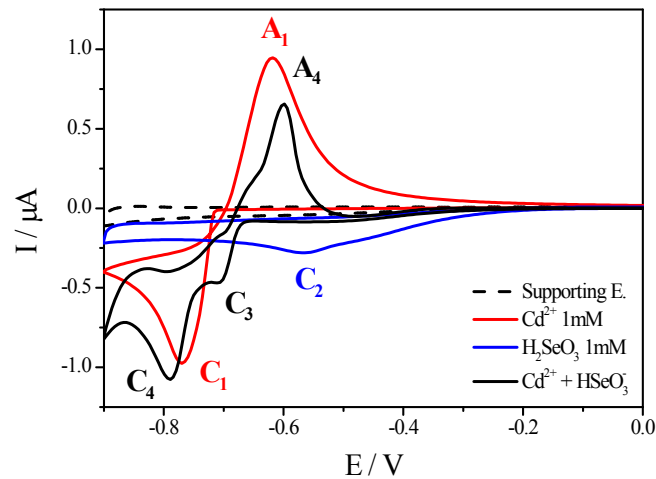
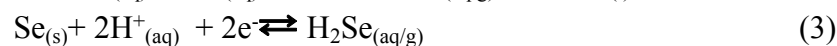
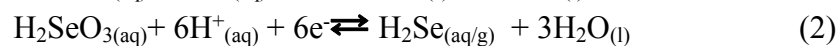
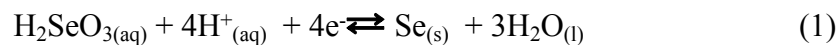
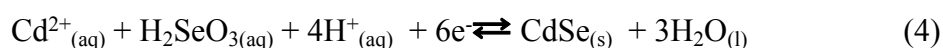


Figure S1 -Cyclic voltammograms on Ti₂ONT and at a scan rate of 50 mV s⁻¹ for H₂SO₄ 0.5 mol L⁻¹(black dashed line),as supporting electrolyte (SE), andSE + 1 mmol L⁻¹solutions of Cd²⁺ (red line), H₂SeO₄(blue line) and Cd²⁺ + H₂SeO₄ (black solid line).

For the CV in the presence of Cd²⁺in SE (red line),one cathodic peak at about -0.77 V (C₁)during the forward scan and one anodic peak at about -0.62 V (A₁) during the reverse scan can be seen. These peaks can be attributed to Cd reduction and dissolution, respectively. For the system containing only Se species in SE (blue line), any anodic peak was evidently observed and, because of this, we believe that the broad cathodic peak (C₂) observed during the forward scan can be associated to these reactions [1,2]:



The voltammetric profile of the binary system can be observed from black solid line CV showed in Figure 1, which had two cathodic peaks (C₃ and C₄) and one anodic peak (A₄). Also, it can be observed that the broad peak attributed to the Se species disappeared, appearing a new cathodic peak at about -0.71 V (C₃). As the free energy of CdSe formation is large negative ($\Delta G^\circ_{\text{f}, 298 \text{ K}} = -141.5 \text{ kJ mol}^{-1}$ [2]), we believe that this process can be related to the reaction 4 showed below[1,2].



The C_4 and A_4 peaks can be respectively associated to Cd^{2+} reduction and dissolution. The peak potential of the C_4 reaction was shifted to more negative potential with Se species presence, probably, the CdSe phase formed at C_3 has become the electrode surface more resistive, inhibiting the Cd reduction. A similar behaviour was observed for Cd dissolution peak, which can be explained in the same way. The charge of the Cd dissolution decreases in relation to the system without Se species, which can be evidence of the CdSe formation.

Thus, the pulsed deposition of CdSe into TiO_2NTs was carried out during 1000 s; the potentials of -0.76 V and -0.64 V were used in the cathodic and anodic pulse and the duration of each pulse per cycle was of 25 s and 15 s, respectively. The anodic pulse was applied to eliminate the Cd excess. The profile of the pulse deposition can be seen in Figure 2.

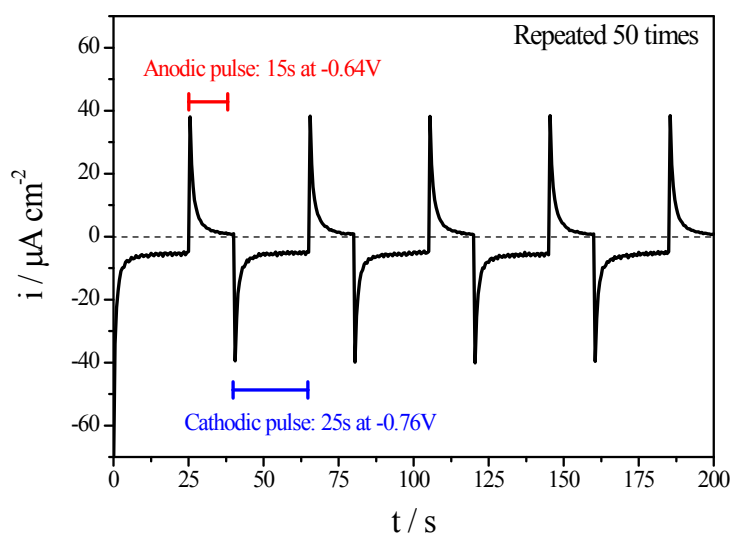


Figure S2 -Chronoamperogram representing the pulsed deposition profile for an electrolytic bath containing $5 \text{ mmol L}^{-1} Cd^{2+}$, $1 \text{ mmol L}^{-1} SeO_2$, and $0.5 \text{ mol L}^{-1} H_2SO_4$ (as supporting electrolyte).

Ordered Desordered CdSe@TiO₂NT TiO₂-anatase Unit Cell

Theoretical calculus involving *density functional theory* (DFT) [3,4] were carried out to elucidate the band structure and correlate theoretical band gap with experimental values.

Based on the results of Rietveld refinement and TiO₂-anatase CIF obtained after the refinement procedure, the crystallographic databasewere used as input in order to compute the referred properties. DFT computations for the geometric and electronic structures of TiO₂ surfaces have been carried out within the generalized gradient approximation (GGA) using PWscf code included in the Quantum-Espresso package[5]. Electron ion interaction were described by ultrasoft pseudopotentialsb[6]. Plane-wave basis set cut-offs for the smooth part of the wave functions was 500 Ry. Electronic structure calculations were performed using a 4 x 4 x 2 Monkhorst-Pack *k*-points grid to sample the Brillouin zone. The resulted TiO₂-anatase for ordered and disordered unit cell can be observed in Figure S3, respectively.

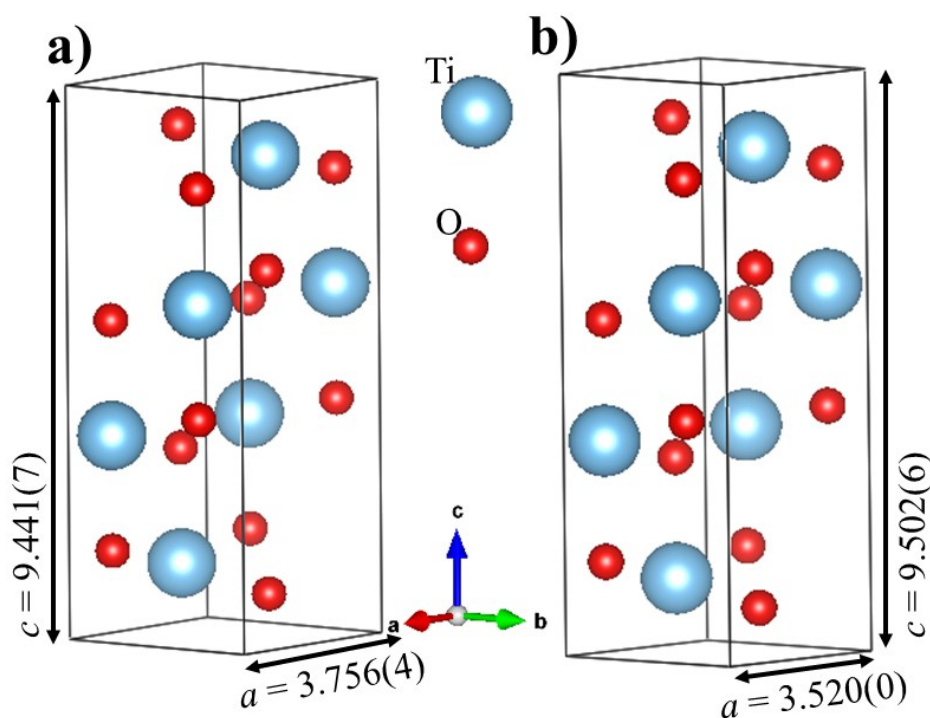


Figure S3 -a) ordered and b) disordered Sample-PTT and Sample-LTT -related TiO₂-anatase unit cell.

TiO₂ Cartesian Coordinates obtained from Rietveld Refinement – Sample-PTT

Ti	0.000000	0.939128	3.541238
Ti	3.756510	0.939128	3.541238
Ti	0.000000	2.817383	5.902062
Ti	3.756510	2.817383	5.902062
Ti	1.878255	2.817383	8.262888
Ti	1.878255	0.939128	1.180413
O	0.000000	0.939128	1.503373
O	3.756510	0.939128	1.503373
O	0.000000	2.817383	7.939927
O	3.756510	2.817383	7.939927
O	1.878255	2.817383	6.225024
O	1.878255	0.939128	3.218277
O	0.000000	2.817383	3.864199
O	3.756510	2.817383	3.864199
O	0.000000	0.939128	5.579102
O	3.756510	0.939128	5.579102
O	1.878255	0.939128	8.585849
O	1.878255	2.817383	0.857452

TiO₂ Cartesian Coordinates obtained from Rietveld Refinement – Sample-LTT

Ti	0.000000	0.947450	3.562387
Ti	3.789800	0.947450	3.562387
Ti	0.000000	2.842350	5.937312
Ti	3.789800	2.842350	5.937312
Ti	1.894900	2.842350	8.312237
Ti	1.894900	0.947450	1.187462
O	0.000000	0.947450	1.795443
O	3.789800	0.947450	1.795443
O	0.000000	2.842350	7.704256
O	3.789800	2.842350	7.704256
O	1.894900	2.842350	6.545293
O	1.894900	0.947450	2.954406
O	0.000000	2.842350	4.170368

- O 3.789800 2.842350 4.170368
- O 0.000000 0.947450 5.329331
- O 3.789800 0.947450 5.329331
- O 1.894900 0.947450 8.920218
- O 1.894900 2.842350 0.579482

References

- [1] P. Bocchetta, M. Santamaria, F. Di Quarto, *Electrochimica Acta* 88 (2013) 340.
- [2] E. B. Chubenko, A. A. Klysho, V. A. Petrovich, V. P. Bondarenko, *Thin Solid Films* 517 (2009) 5981.
- [3] P. Hohenberg, W. Kohn, *Physics Review* 136(1964) B864.
- [4] W. Kohn, L. J. Sham, *Physics Review* 140 (1965) A1133.
- [5] P. Giannozzi, S. Baroni, N. Bonini, M. Calandra, R. Car, C. Cavazzoni, D. Ceresoli, G. L Chiarotti, M. Cococcioni, I. Dabo, A. Dal Corso, S. de Gironcoli, S. Fabris, G. Fratesi, R. Gebauer, U. Gerstmann, C. Gougoussis, A. Kokalj, M. Lazzeri, L. Martin-Samos , N. Marzari, F. Mauri, R. Mazzarello, S. Paolini, A. Pasquarello, L. Paulatto, C. Sbraccia, S. Scandolo, G. Sclauzero, A. P Seitsonen, A. Smogunov, P. Umari, R. M Wentzcovitch, *Journal of Physics: Condensed Matter* 21 (2009) 395502.
- [6] D. Vanderbilt, *Phys. Rev. B* 4 (1990) 7892.